

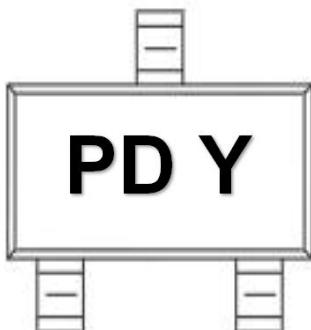
## P-Channel 50-V(D-S) MOSFET

V(BR)DSS	RDS(on)MAX	ID
-50 V	4Ω@10V	-130mA
	5Ω@4.5V	

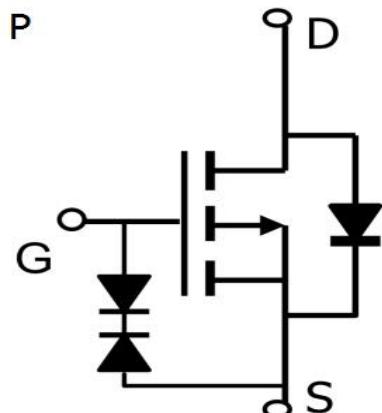
### FEATURE:

- Energy Efficient
- Low Threshold Voltage
- High-speed Switching
- Miniature Surface Mount Package Saves Board Space
- ESD Protected

### MARKING:



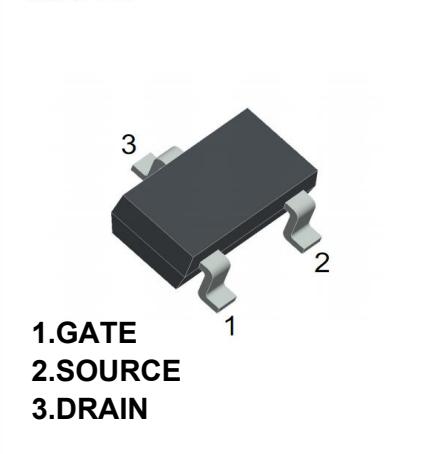
### Equivalent Circuit:



### APPLICATION:

※ DC-DC converters, load switching, power management in portable and battery-powered products such as computers, printers, cellular and cordless telephones.

### SOT-23



### Mosfet Maximum ratings ( Ta=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	VDS	-50	V
Gate-Source Voltage	VGS	±20	
Continuous Drain Current	ID	-130	mA
Pulsed Drain Current (note 1) @tp <10 μs	IDM	-520	
Power Dissipation	PD	225	mW
Thermal Resistance from Junction to Ambient	R <sub>θJA</sub>	556	°C/W
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature	T <sub>STG</sub>	-55~+150	°C
Maximum Lead Temperature for Soldering Purposes , Duration for 5 Seconds	TL	260	°C

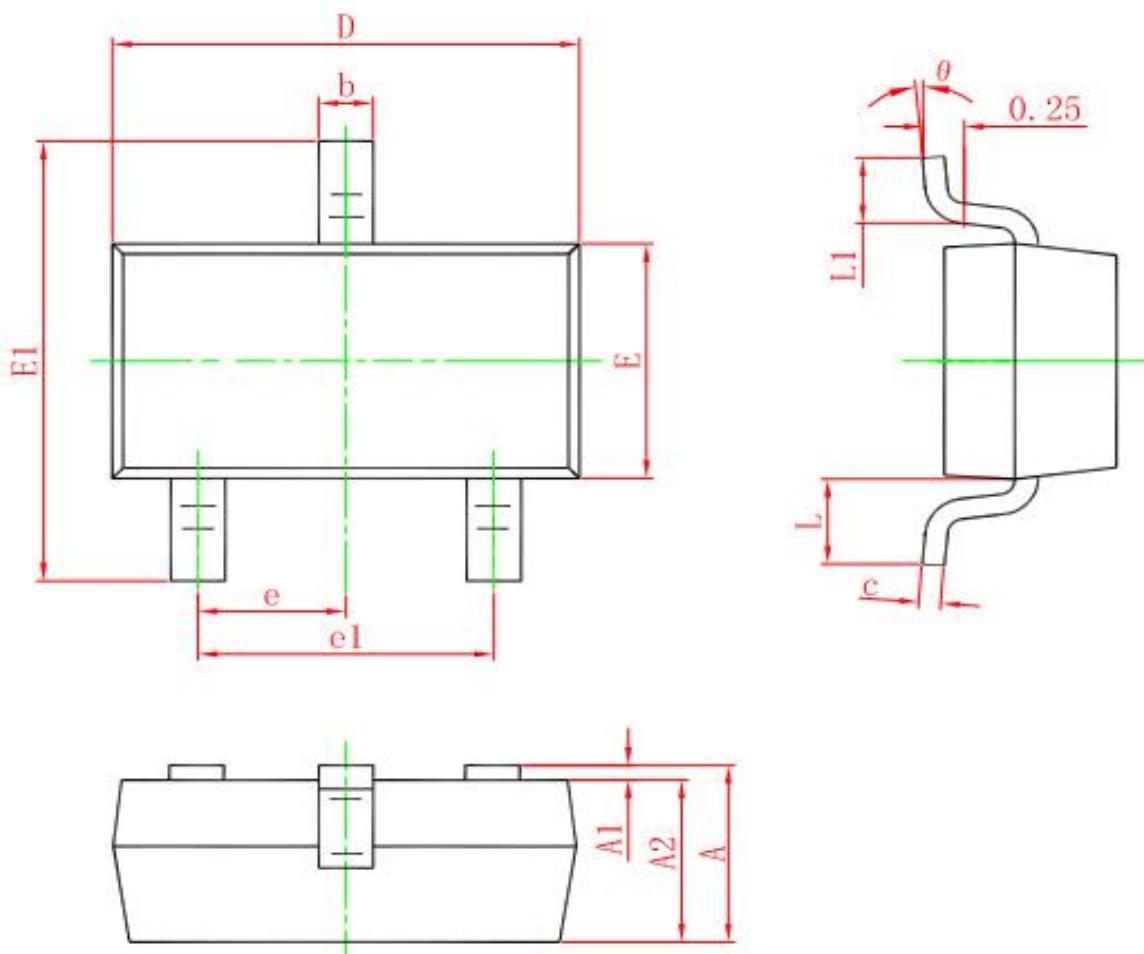
**MOSFET ELECTRICAL CHARACTERISTICS**

unless otherwise specified  $T_a = 25^\circ C$ 

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
<b>Static Characteristics</b>						
Drain-source breakdown voltage	V(BR)DSS	$V_{GS} = 0V, ID = -250\mu A$	-50			V
Gate-threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, ID = -250\mu A$	-1		-2	V
Gate-body leakage	$I_{GSS}$	$V_{DS} = 0V, V_{GS} = \pm 20V$			$\pm 10$	$\mu A$
Zero gate voltage drain current	$I_{DSS}$	$V_{DS} = -50V, V_{GS} = 0V$			-15	$\mu A$
Drain-source on-resistancea	RDS(on)	$V_{GS} = -10V, ID = -100mA$		1.9	4	$\Omega$
		$V_{GS} = -4.5V, ID = -100mA$		2.4	5	$\Omega$
Forward transconductancea	$g_{fs}$	$V_{DS} = -10V, ID = -100mA$	50			S
Diode forward voltage	$V_{SD}$	$I_S = -0.13A, V_{GS}=0V$		-0.8	-1.3	V
<b>Dynamic Characteristics</b>						
Input capacitance	$C_{iss}$	$V_{DS} = -5V, V_{GS} = 0V, f=1MHz$		30		pF
Output capacitance	$C_{oss}$			10		pF
Reverse transfer capacitanceb	$C_{rss}$			5		pF
<b>Switching Characteristics</b>						
Turn-on delay time	$t_{d(on)}$	$V_{DD} = -15V$ $RL = 5\Omega, ID = -50mA,$		2.5		ns
Rise time	$t_r$			1		ns
Turn-off delay time	$t_{d(off)}$			16		ns
Fall time	$t_f$			8		ns
<b>SOURCE-DRAIN DIODE CHARACTERISTICS</b>						
Continuous Current	$I_S$				-0.13	A
Pulsed Current	$I_{SM}$				-0.52	A

**Note :**

- 1.Repetitive rating : Pulse width limited by junction temperature.
- 2.Surface mounted on FR4 board ,  $t \leq 10s$ .
- 3.Pulse Test : Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
- 4.Guaranteed by design, not subject to producting.

**SOT-23 PACKAGE OUTLINE DIMENSIONS**

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP.		0.037 TYP.	
e1	1.800	2.000	0.071	0.079
L	0.550 REF.		0.022 REF.	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°